

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Patent Application Serial No. Unknown
 Filing Date April 8, 2004
 Inventor Gurtej S. Sandhu et al.
 Assignee Micron Technology, Inc.
 Group Art Unit Unknown
 Examiner Unknown
 Attorney Docket No. MI22-2268
 Customer No. 021567
 Title: Methods of Forming a Reaction Product and Methods of Forming a
 Conductive Metal Silicide by Reaction of Metal With Silicon

INFORMATION DISCLOSURE STATEMENT

References -- See Attached Form PTO-1449

The attached form PTO-1449 is submitted in compliance with
 37 CFR §1.56. Pursuant to 1276 OG 55, August 5, 2003, no copies of cited U.S.
 patents or U.S. patent application publications are included, as the date of filing
 of this patent application occurs after June 30, 2003. Copies of all other
 references are attached. No admission is made regarding whether all the listed
 references are prior art.

Respectfully submitted,

Dated: 4-8-04By: 

Mark S. Matkin
 Reg. No. 32,268

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. MI22-2268		SERIAL NO. Unknown	
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT: Gurtej S. Sandhu et al.			
				FILING DATE April 8, 2004		GROUP Unknown	

U.S. PATENT DOCUMENTS							
*Examiner's Initials		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	AA	4,622,735	11/18/86	Shibata			
	AB	4,683,645	08/04/87	Naguib et al.			
	AC	5,236,865	08/17/93	Sandhu et al.			
	AD	5,444,024	08/22/95	Anjum et al.			
	AE	5,470,794	11/28/95	Anjum et al.			
	AF	10/689,958		Basceri			10/20/03
	AG	10/690,029		Derderian et al.			10/20/03
	AH						

FOREIGN PATENT DOCUMENTS								
		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
	AI							
	AJ							

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)			
	AK		ABSTRACT: Basceri et al., <i>Atomic Layer Deposition for Nanoscale CU Metalization</i> , 10 pages (pre-April 2004).
	AL		En et al., <i>Plasma immersion ion implantation reactor design considerations for oxide charging</i> , 85 SURFACE AND COATINGS TECHNOLOGY 64-69 (1966).
	AM		Ku et al., <i>The Application of Ion Beam Mixing, Doped Silicide, and Rapid Thermal Processing of Self-Aligned Silicide Technology</i> , 137 J. Electrochem. Soc. No. 2, pp. 728-740 (February 1990).
	AO		Rubin et al., <i>Shallow-Junction Diode Formation by implantation of Arsenic and Boron Through Titanium-Silicide Films and ...</i> , 17 IEEE Transactions on Electron Devices, No. 1, pp. 183-190 (January 1990).
EXAMINER		DATE CONSIDERED	

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.